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## CLEAN VERSION OF ALL PENDING CLAIMS

A method for making a transistor containing a gate I. (Twice amended) dielectric structure, comprising: providing a gate conductor; providing a channel and providing, between the gate conductor and the channel, an oxide layer of the gate dielectric structure by an in-sith steam generation process. 2. (Cancelled) The method of claim 1, wherein the transistor is a thin film 3. (Amended) transistor. 4. (Cancelled) 5. (Amended) The method of claim 3, wherein the in-situ steam generation process is performed at a temperature ranging from about 600 to about 900 degrees Celsius. 6. The method of claim 1, wherein the in-situ steam generation process is performed at a pressure ranging from about 100 millitorr to about 760 torr. 7. The method of claim 1, wherein the in-situ steam generation process is performed for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms. 8. (Amended) The method of claim 28, further including annealing the oxide layer in a nitric oxide atmosphere. 9. (Twice amended) A method for making a SONOS device, comprising:

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providing a channel region;

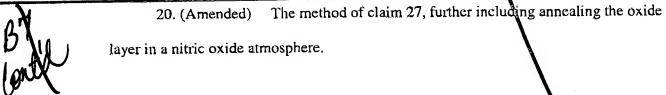
providing a first oxide layer on the channel region by an in-situ steam generation

process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

- 10. (Cancelled)
- 11. (Cancelled)
- 12. The method of claim 9, wherein the in-situ steam generation process is performed at a temperature ranging from about \$\infty 50\$ to about 1050 degrees Celsius.
- 13. The method of claim 9, wherein the in-situ steam generation process is performed at a pressure ranging from about 100 millitorr to about 760 torr.
- 14. The method of claim 9, wherein the in-situ steam generation process is performed for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms.
- 15. The method of claim 9, further including annealing the oxide layer in a nitric oxide atmosphere.
  - 16. (Cancelled)
  - 17. (Cancelled)
  - 18. (Cancelled)
  - 19. (Cancelled)





21. (Amended) A method for making a gate dielectric structure for a SONOS device, comprising:

providing silicon;

providing an oxide layer of a gate dielectric structure on the silicon by in-situ steam generation, the oxide layer having a thickness of about 10 to about 200 angstroms; and

annealing the oxide layer in a nitric oxide atmosphere.

22. (Amended) A method for making a gate dielectric structure for a thin film transistor or a SONOS device, comprising:

providing a gate conductor

providing a channel region; and

providing, between the gate conductor and the channel region, an oxide layer of a gate dielectric structure by an in-situ steam generation process performed at a temperature ranging from about 600 to about 1050 degrees Celsius, a pressure ranging from about 100 millitorr to about 760 torr, and for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms.

23. (Amended) A thin film transistor containing a gate dielectric structure made by a method comprising:

providing a gate conductor;

providing a channel region; and

providing, between the gate conductor and the channel region, an oxide layer of the gate dielectric structure on the channel region by an in-sitursteam generation process.



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A SONOS semiconductor device made by a method 24. (Twice amended) comprising: providing a channel region; providing a first oxide layer on the channel region by an in-situ steam generation process; providing a nitride layer on the first oxide layer; and providing a second oxide layer on the nitride layer. An integrated circuit containing a thin film transistor with a 25. (Amended) ate dielectric structure made by a method comprising: providing a gate conductor providing a channel; and providing, between the gate conductor and the channel, an oxide layer of the gate dielectric structure by an in-situ steam generation process. An integrated circuit containing a SONOS semiconductor 26. (Twice amended) device made by a method comprising: providing a silicon wafer or silicon layer; providing a first oxide layer on the silicon wafer or silicon layer by an in-situ steam generation process; providing a nitride layer on the first oxide layer; and providing a second oxide layer on the nitride layer. The method of claim 1, wherein the transistor is a SONOS transistor. 27. (New) The method of claim 3, wherein the transistor is a SONOS transistor. 28. (New)

29. (New) The method of claim 3, wherein the transistor comprises a floating

gate.

30. (New) The method of daim 21, wherein the silicon is a surface of a silicon

wafer.

31. (New) The method of claim 21, wherein the silicon comprises polysilicon.

32. (New) The transistor of claim 23, wherein the transistor comprises a

floating gate.

33. (New) The integrated circuit of claim 25, wherein the transistor comprises a

floating gate.

34. (New) The transistor of claim 27 wherein the gate conductor comprises

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